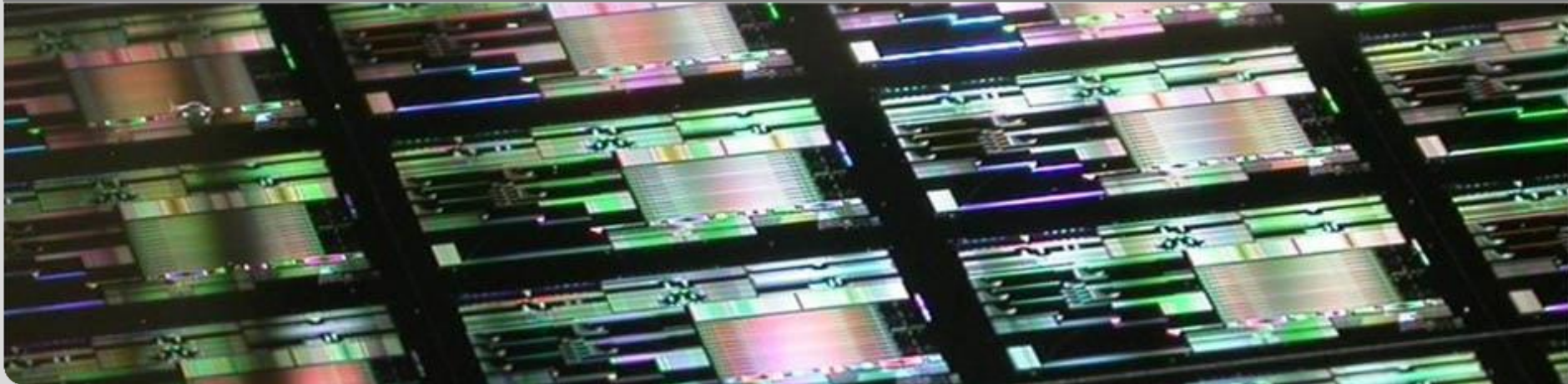


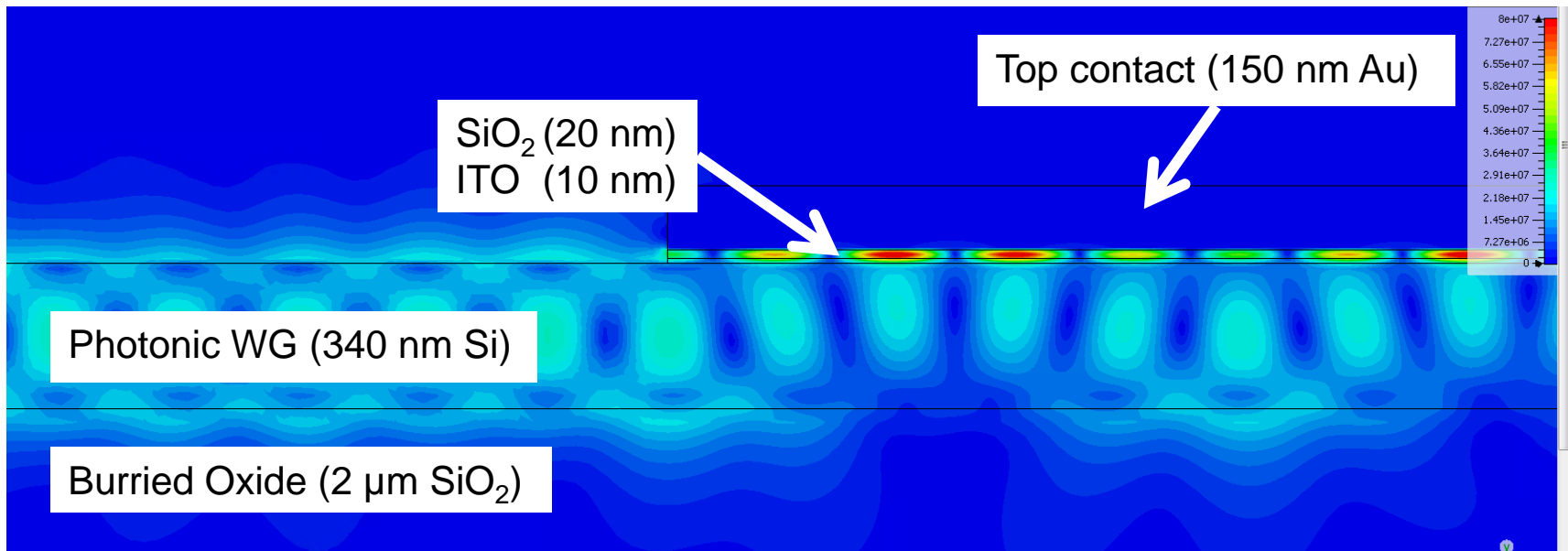
**NAVOLCHI TelConf. 02.12.2013**

# **Surface Plasmon Polariton Absorption Modulator (SPPAM)**

Institute of Photonics and Quantum Electronics (IPQ), Karlsruhe, Germany  
Institute of Microstructural Technology, Karlsruhe, Germany  
Institute of Electromagnetic Fields (IFH), ETH Zurich, Switzerland

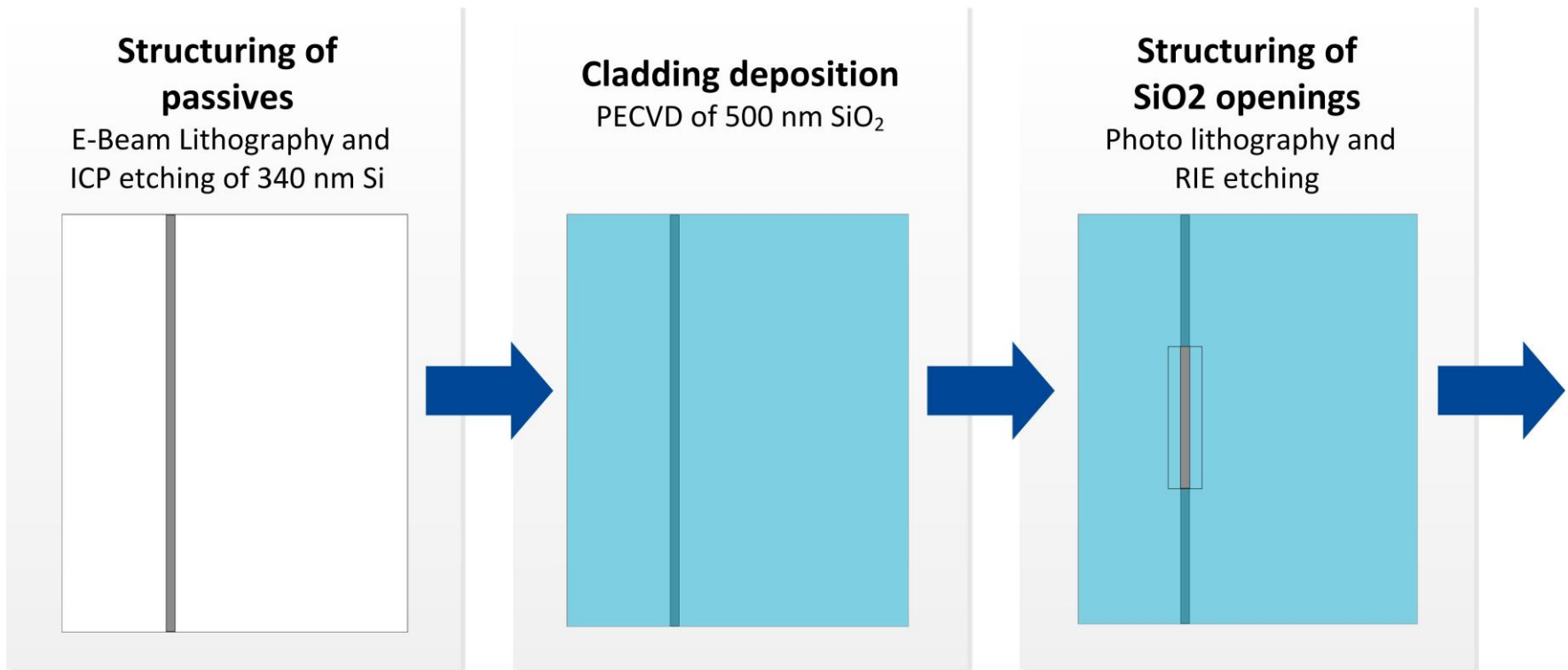


Electric Field (CST simulations), here no voltage applied

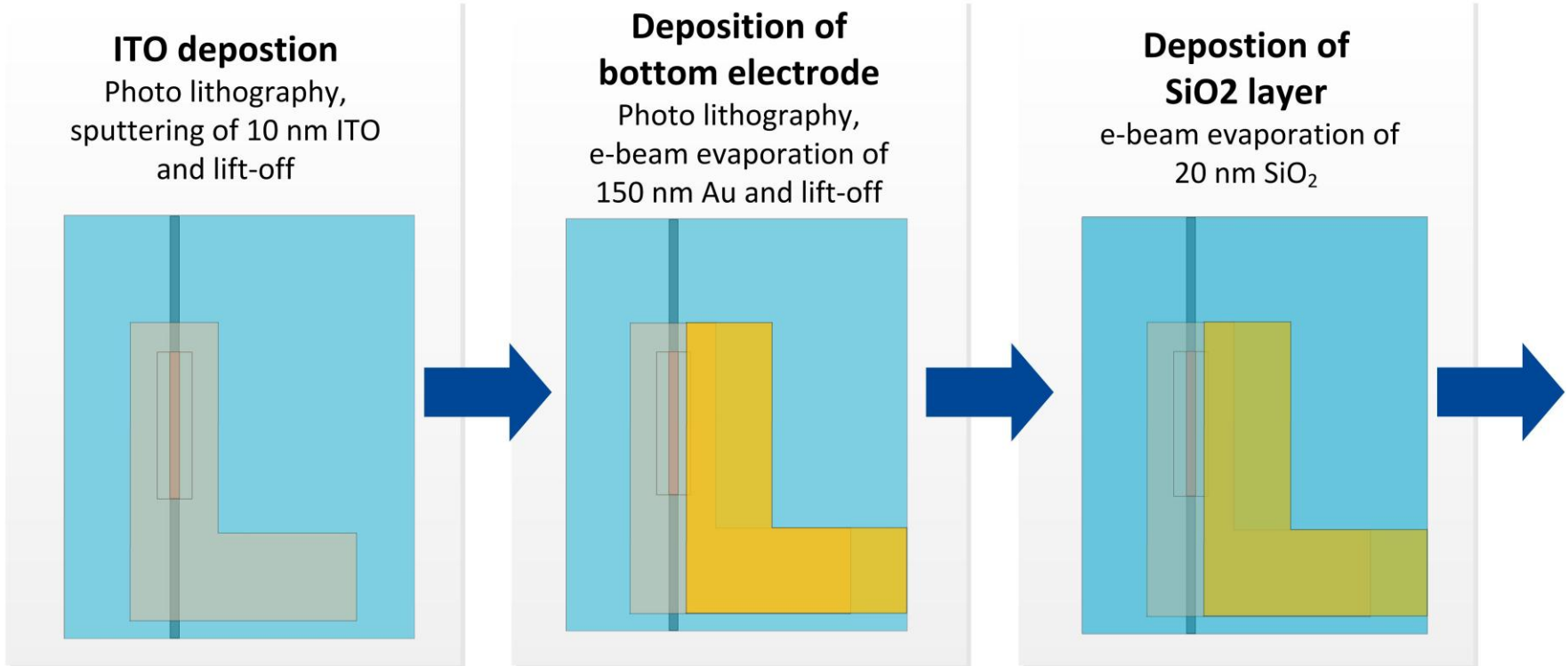


Working principle: carrier density of ITO may be switched by applying an electric field → absorption of ITO modulated

# Fabrication Process



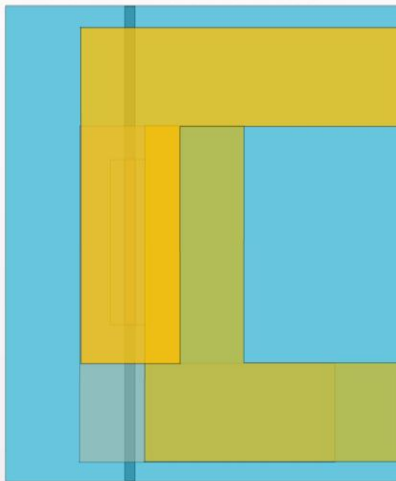
# Fabrication Process



# Fabrication Process

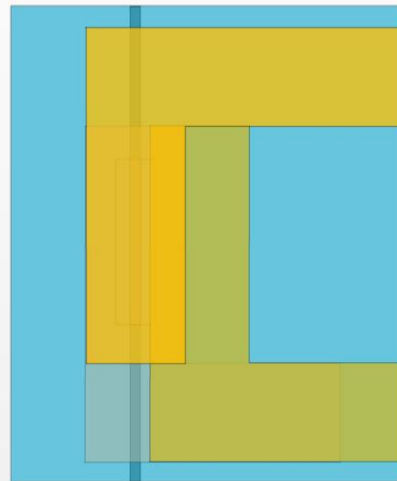
## Deposition of top electrode

Photo lithography,  
e-beam evaporation of  
150 nm Au and lift-off

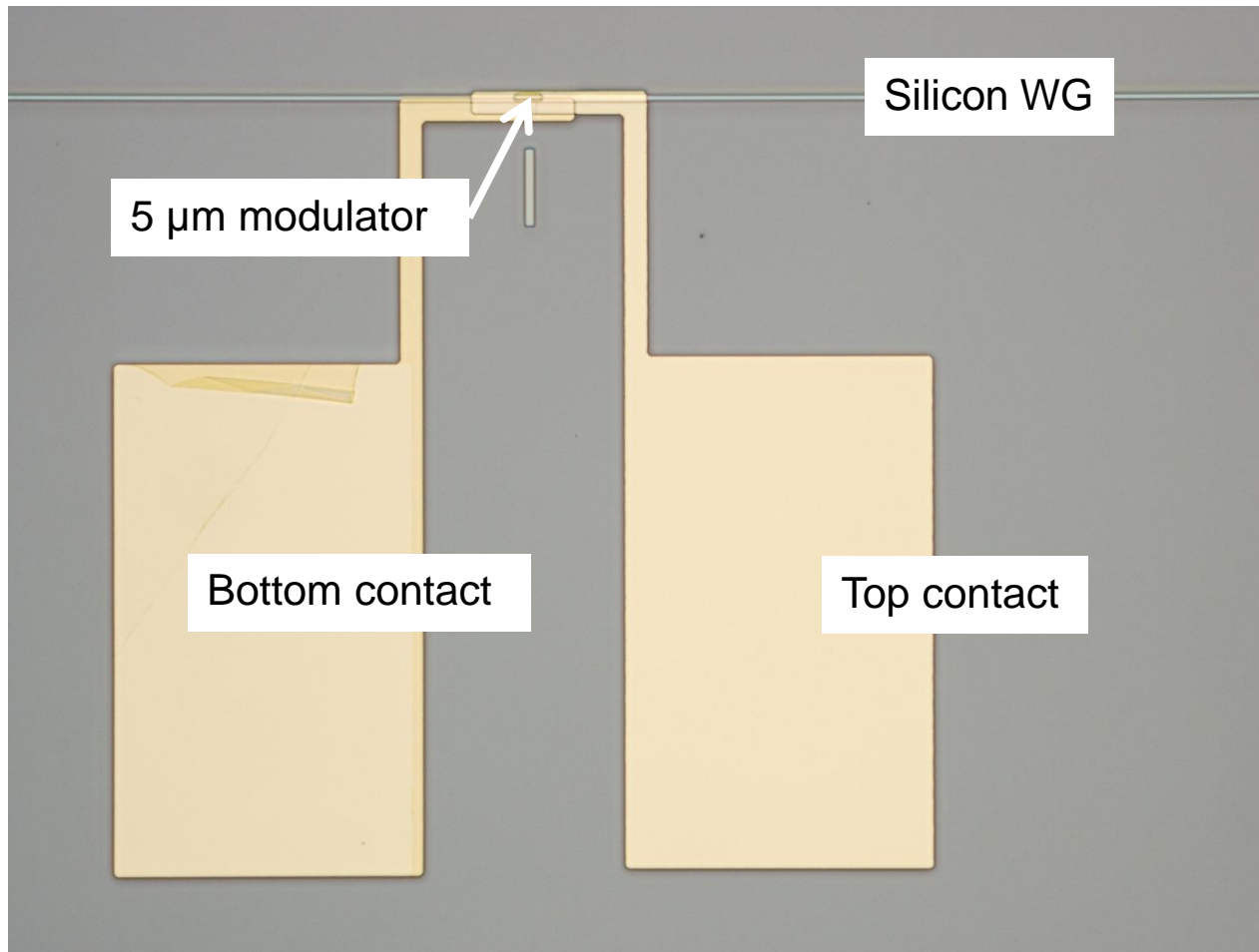


## Opening of SiO<sub>2</sub>

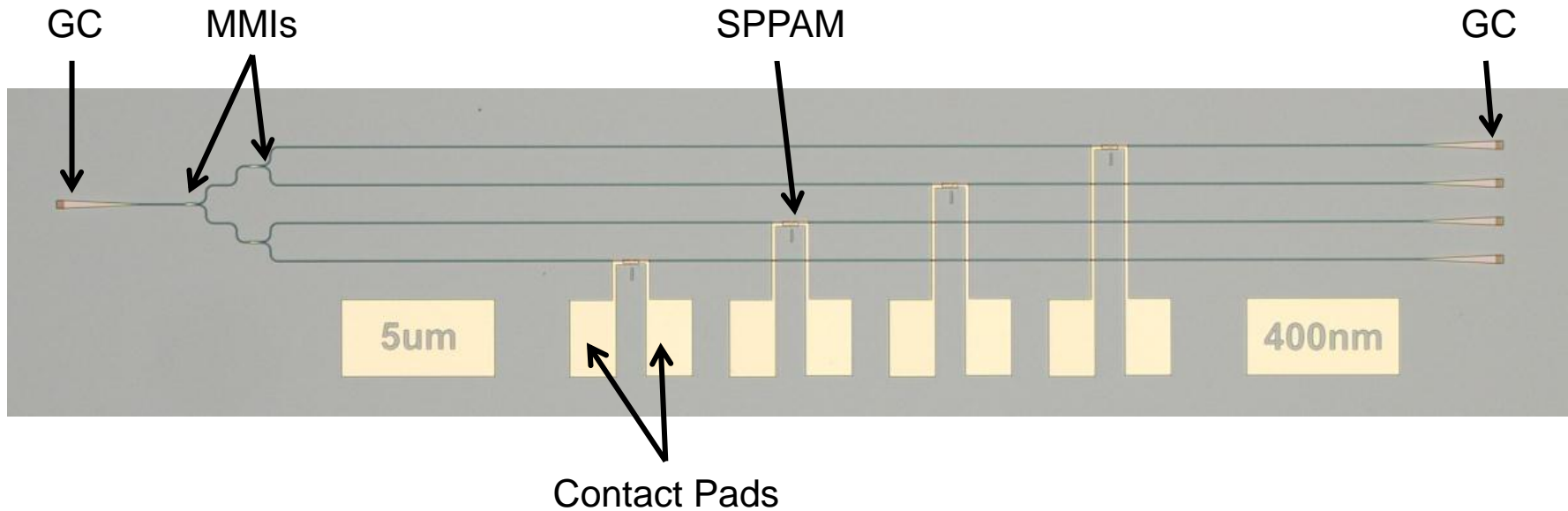
Photo lithography and  
RIE etching



# Optical Microscope Image Single Device

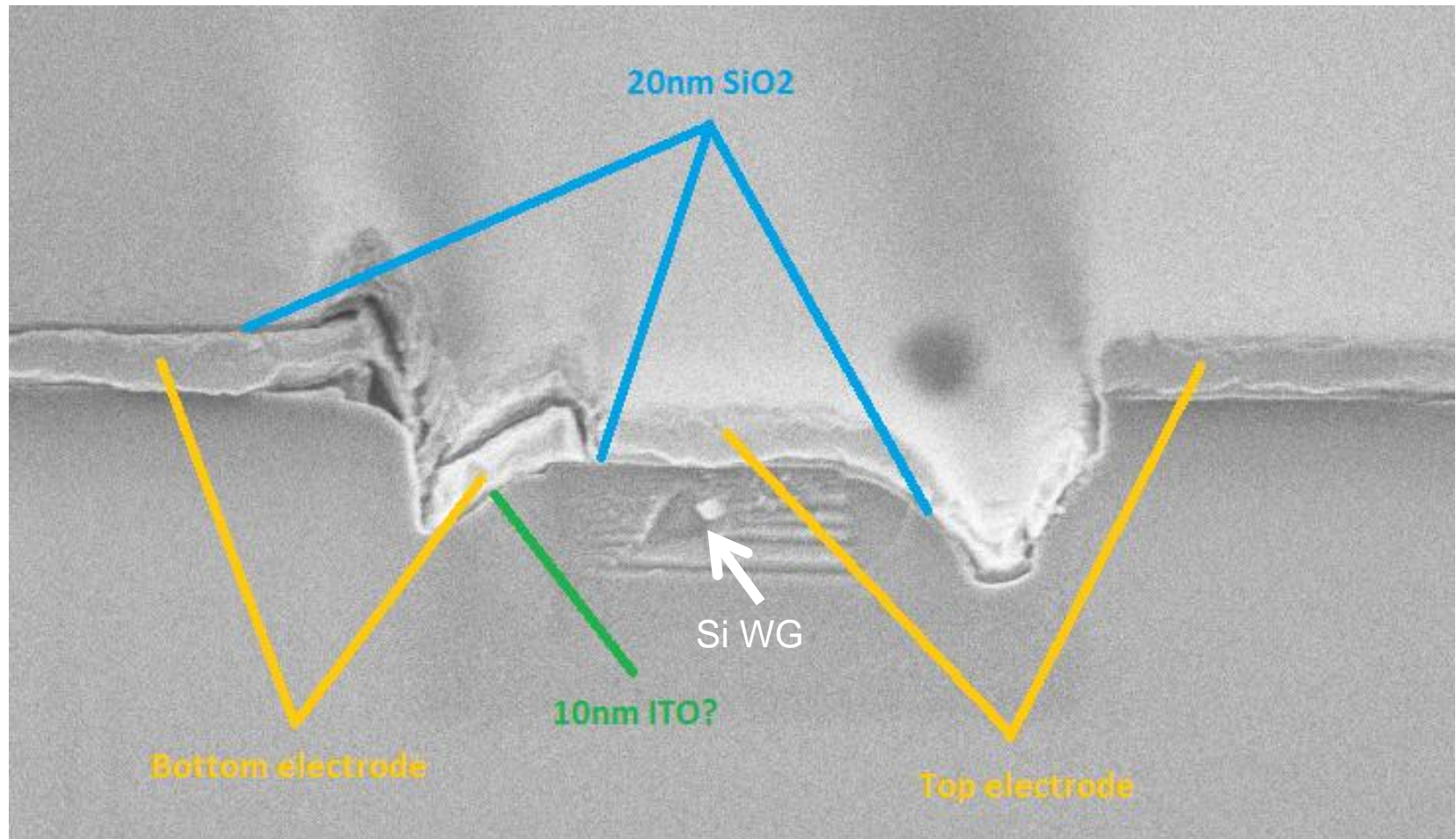


# Optical Microscope Image Four Channel Array (50 $\mu\text{m}$ pitch)



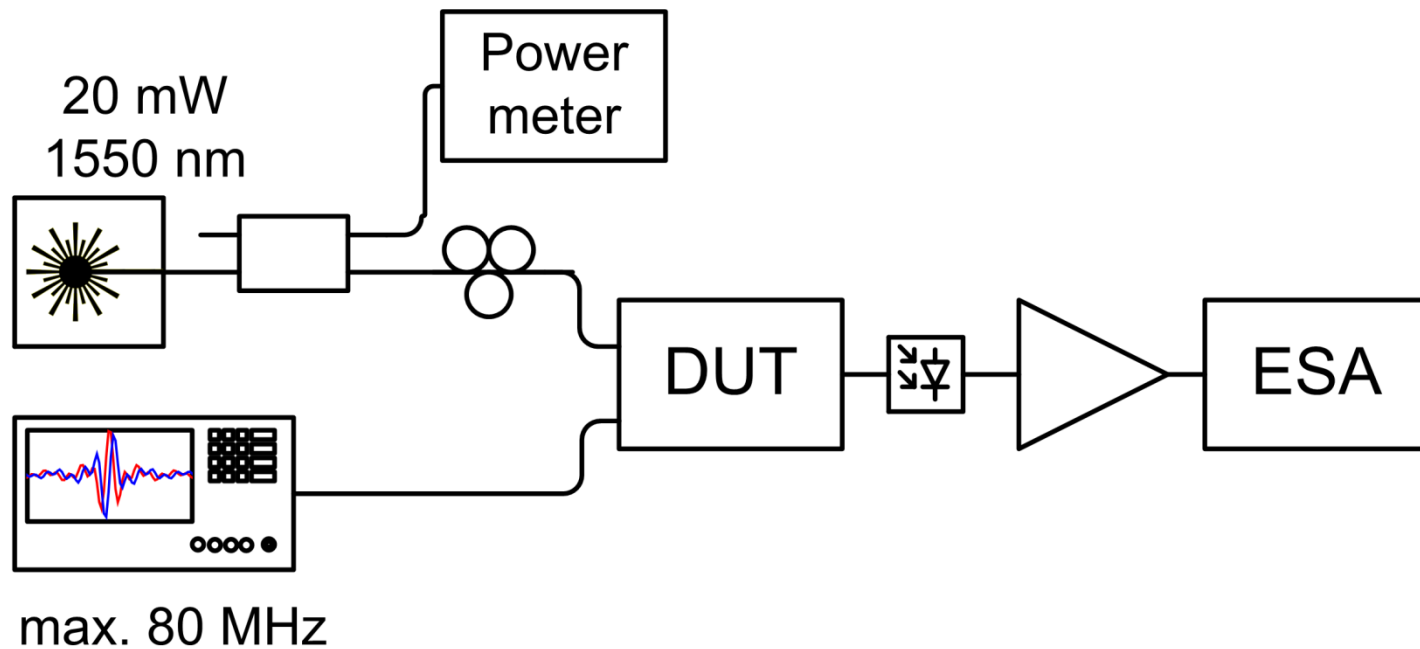
- Arrays of 2 and 4 channels with pitches of 35  $\mu\text{m}$ , 50  $\mu\text{m}$ , 250  $\mu\text{m}$
- 3, 5, 10, 20  $\mu\text{m}$  long devices

# SEM Image Cross Section





# Characterization (in progress)



# Characterization (in progress)

10 $\mu$ m long device, sin  $\pm 1$  V, 80 MHz

